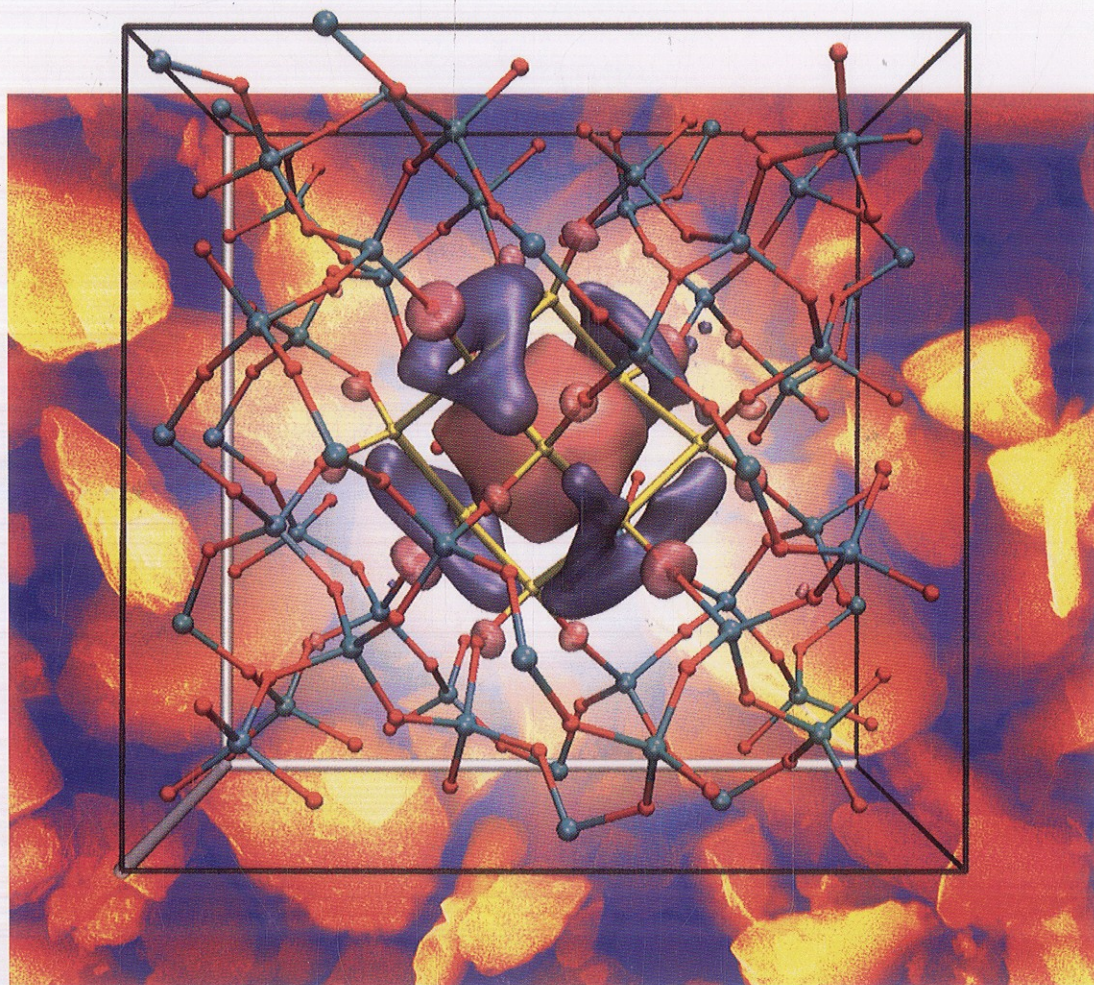


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 WILEY-VCH

Silicon Nanocrystals

Fundamentals, Synthesis and Applications



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